



Docket No.: 50369

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANT: E. Pavelchek

EXAMINER: M. Kornakov

SERIAL NO.: 09/330,417

GROUP: 1746

FILED: June 11, 1999

FOR: ANTIREFLECTIVE HARD MASK COMPOSITIONS

24/C
AS
3/26/3
RECEIVED
MAR 26 2003
GROUP 1700

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

Sir:

AMENDMENT

Applicant is in receipt of the Office Action of September 12, 2002. Please amend the above-identified application as follows.

IN THE CLAIMS

Please cancel claims 1, 4-12, 14-17, 20 and 24-33 without prejudice.

Please add the following new claims.

- C1
34. A method for forming a photoresist relief image, comprising:
- (a) providing an integrated circuit substrate having a dielectric layer thereon;
 - (b) over the dielectric layer, applying a coating layer of an organic antireflective composition that comprises a component with Si substitution;
 - (c) applying a coating layer of a photoresist composition over the antireflective composition layer;
 - (d) exposing to patterned radiation and developing the photoresist composition coating layer to form a photoresist relief image.

35. The method of claim 34 wherein the antireflective composition comprises an

organosilicon resin.

03/27/2003 ASINGLET 00000001 041105 09330417

01 FC:1202 360.00 CH
02 FC:1203 280.00 CH